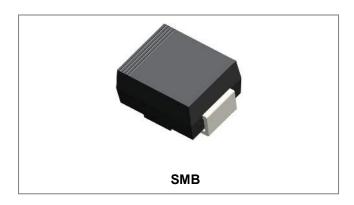






SK220 SCHOTTKY RECTIFIER



Features

- Schottky Barrier Chip
- Guard Ring Die Construction for Transient Protection
- High Current Capability
- Low Power Loss, High Efficiency
- High Surge Current Capability
- For Use in Low Voltage, High Frequency Inverters, Free Wheeling, and Polarity Protection Applications
- This is a Pb Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Circuit Diagram



Applications

- Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection
- Disk drives
- Battery charging

Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} V _R	-	200	V
Average Rectified Forward Current	I _{F (AV)}	50% duty cycle @T _C =105°C, rectangular wave form	2	Α
Peak One Cycle Non-Repetitive Surge Current	I _{FSM}	8.3ms, Half Sine pulse, T _c = 25 °C	50	Α

Electrical Characteristics:

Characteristics	Symbol	Condition	Тур.	Max.	Units
Forward Voltage Drop*	V _{F1}	@ 2A, Pulse, T _A = 25 °C	0.88	0.90	V
Reverse Current*	I _{R1}	@V _R = rated V _R , T _A = 25 °C	0.05	1	mA
	I _{R2}	@V _R = rated V _R , T _A = 100 °C	-	20	mA
Junction Capacitance	Ст	$@V_R = 5V, T_C = 25 ^{\circ}C, f_{SIG} = 1MHz$	150	170	pF
Series Inductance	Ls	Measured lead to lead 5 mm from package body	8.0	-	nH
Voltage Rate of Change	dv/dt	-	-	10,000	V/μs

^{*} Pulse width < 300 µs, duty cycle < 2%

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Thermal-Mechanical Specifications:

Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	TJ	-	-55 to +150	°C
Storage Temperature	T _{stg}	-	-55 to +150	°C
Typical Thermal Resistance Junction to Lead	$R_{ heta JL}$	DC operation	23	°C/W
Typical Thermal Resistance Junction to Ambient	$R_{ heta JA}$	DC operation	88	°C/W
Approximate Weight	wt	-	0.09	g

Ratings and Characteristics Curves

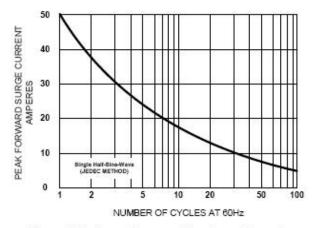


Figure 1. Maximum Non-repetitive Surge Current

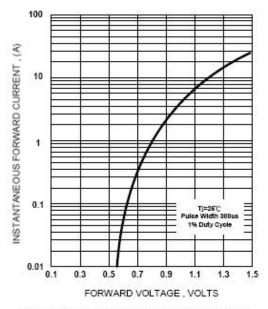


Figure 3. Typical Forward Characteristics

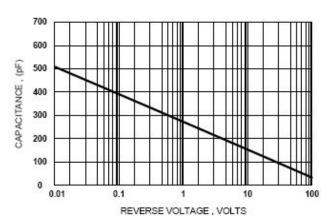
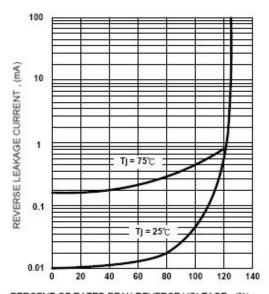


Figure 2. Typical Junction Capacitance



PERCENT OF RATED PEAK REVERSE VOLTAGE , (%)

Figure 4. Typical Reverse Characteristics

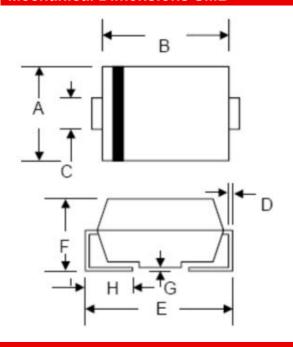
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Mechanical Dimensions SMB



SYMBOL	Millin	neters	Inches		
SYMBOL	Min.	Max.	Min.	Max.	
А	3.30	3.94	0.130	0.155	
В	4.06	4.70	0.160	0.185	
С	1.80	2.20	0.071	0.087	
D	0.152	0.305	0.006	0.012	
Е	4.80	5.59	0.189	0.220	
F	2.10	2.60	0.083	0.102	
G	0.051	0.203	0.002	0.008	
Н	0.76	1.52	0.030	0.060	

Ordering Information

Device	Package	Shipping	
SK220	SMB (Pb-Free)	3000pcs / reel	

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

Marking Diagram

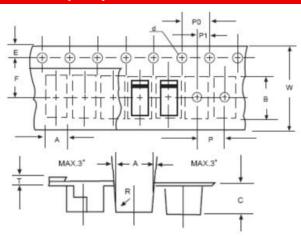
SK220 XXXXX Where XXXXX is YYWWL

SK = Device Type 2 = Forward Current (2A) 20 = Reverse Voltage (200V)

YY = Year WW = Week L = Lot Number

Cautions: Molding resin Epoxy resin UL:94V-0

Carrier Tape Specification SMB



SYMBOL	Millimeters		
	Min.	Max.	
Α	2.97	3.17	
В	5.70	5.90	
O	2.32	2.52	
d	1.40	1.60	
E	1.40	1.60	
F	5.60	5.70	
Р	3.90	4.10	
P0	3.90	4.10	
P1	1.90	2.10	
Т	0.25	0.35	
W	11.80	12.20	

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